

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	2
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Complete If Known

Application Number	10/816,282
Filing Date	March 31, 2004
First Named Inventor	Peter L.D. Chang
Art Unit	2818
Examiner Name	Ho, Tu Tu V.
Attorney Docket Number	42P18252

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

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**Examiner
Signature**

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Date	
Considered	

Dec-2005

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Based on PTO/SB/D8A (08-03) as modified by Blakely, Solokoff, Taylor & Zelman (w/ 08/11/2003).

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.†	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
TH		Nowak EJ, et al., "Turning Silicon On Its Edge - Overcoming silicon scaling barriers with double-gate and FinFET technology," IEEE Circuits and Devices Mag. vol. 20, no. 1, January 2004, pgs 20-31.	
TH		Fried, DM, et al. "Improved Independent Gate N-Type FinFET Fabrication and Characterization," IEEE Electron Device Letters, vol. 24, no. 9, September 2003, pages 592-594.	
TH		Fried, DM, et al. "A Fin-Type Independent-Double-Gate NFET," Device Research Conference, 2003 June, IEEE, 23 June 2003, pages 45-46.	
TH		PCT Search Report, Int'l application no. PCT/US2005/010164, mailed 07-27-2005, 5 pgs.	

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